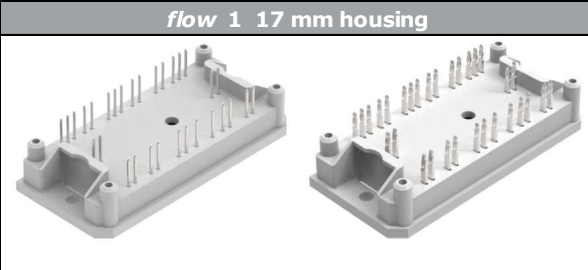
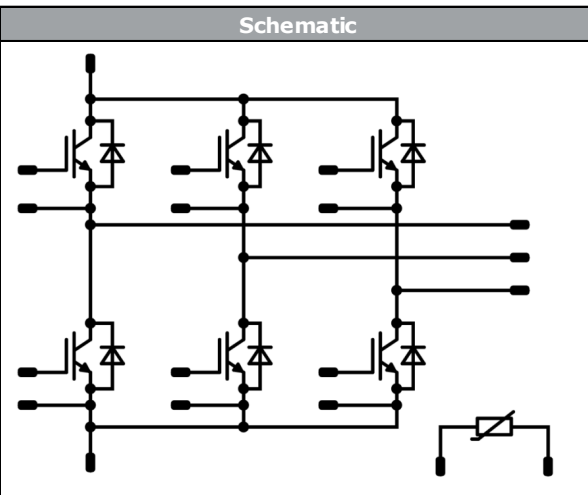




Vincotech

| <i>flow PACK 1</i> | 1200 V / 35 A |
|---|---|
| <div style="border: 1px solid black; padding: 5px; margin-bottom: 5px;"> <p style="text-align: center; margin: 0;">Features</p> <ul style="list-style-type: none"> IGBT M7 technology with low V_{CESat} and improved EMC behavior Compact and low inductive design Built-in NTC </div> <div style="border: 1px solid black; padding: 5px; margin-bottom: 5px;"> <p style="text-align: center; margin: 0;">Target applications</p> <ul style="list-style-type: none"> Industrial Drives UPS </div> <div style="border: 1px solid black; padding: 5px;"> <p style="text-align: center; margin: 0;">Types</p> <ul style="list-style-type: none"> 10-F1126PA035M7-L827F09 10-P1126PA035M7-L827F09Y </div> | <div style="border: 1px solid black; padding: 5px; margin-bottom: 5px;"> <p style="text-align: center; margin: 0;"><i>flow 1 17 mm housing</i></p>  </div> <div style="border: 1px solid black; padding: 5px;"> <p style="text-align: center; margin: 0;">Schematic</p>  </div> |

Maximum Ratings

$T_j = 25\text{ °C}$, unless otherwise specified

| Parameter | Symbol | Condition | Value | Unit |
|-----------------------------------|------------|---------------------------------------|-------|------|
| Inverter Switch | | | | |
| Collector-emitter voltage | V_{CES} | | 1200 | V |
| Collector current | I_C | $T_j = T_{jmax}$ $T_s = 80\text{ °C}$ | 35 | A |
| Repetitive peak collector current | I_{CRM} | t_p limited by T_{jmax} | 70 | A |
| Total power dissipation | P_{tot} | $T_j = T_{jmax}$ $T_s = 80\text{ °C}$ | 107 | W |
| Gate-emitter voltage | V_{GES} | | ±20 | V |
| Maximum junction temperature | T_{jmax} | | 175 | °C |



Maximum Ratings

$T_j = 25\text{ °C}$, unless otherwise specified

| Parameter | Symbol | Condition | Value | Unit |
|-------------------------------------|------------|---------------------------------------|-------|------|
| Inverter Diode | | | | |
| Peak repetitive reverse voltage | V_{RRM} | | 1200 | V |
| Continuous (direct) forward current | I_F | $T_j = T_{jmax}$ $T_s = 80\text{ °C}$ | 35 | A |
| Repetitive peak forward current | I_{FRM} | T_j limited by T_{jmax} | 70 | A |
| Total power dissipation | P_{tot} | $T_j = T_{jmax}$ $T_s = 80\text{ °C}$ | 75 | W |
| Maximum junction temperature | T_{jmax} | | 175 | °C |

Module Properties

Thermal Properties

| | | | | |
|---|-----------|--|---------------------------|----|
| Storage temperature | T_{stg} | | -40...+125 | °C |
| Operation temperature under switching condition | T_{jop} | | -40...($T_{jmax} - 25$) | °C |

Isolation Properties

| | | | | |
|----------------------------|------------|-------------------------------------|-----------|----|
| Isolation voltage | V_{isol} | DC Test Voltage* $t_p = 2\text{ s}$ | 6000 | V |
| | | AC Voltage $t_p = 1\text{ min}$ | 2500 | V |
| Creepage distance | | | min. 12,7 | mm |
| Clearance | | | 12,64 | mm |
| Comparative Tracking Index | CTI | | > 200 | |

*100 % tested in production



Characteristic Values

| Parameter | Symbol | Conditions | | | | | Value | | | Unit |
|-----------|--------|--------------|--------------|--------------|-----------|------------|-------|-----|-----|------|
| | | V_{GS} [V] | V_{GE} [V] | V_{DS} [V] | I_D [A] | T_j [°C] | Min | Typ | Max | |

Inverter Switch

Static

| Parameter | Symbol | $V_{GE} = V_{CE}$ | V_{GS} [V] | V_{GE} [V] | V_{DS} [V] | I_D [A] | T_j [°C] | Min | Typ | Max | Unit |
|--------------------------------------|--------------|-------------------|--------------|--------------|--------------|-----------|------------------|-----|----------------------|------|----------|
| Gate-emitter threshold voltage | $V_{GE(th)}$ | | | | | 0,0035 | 25 | 5,4 | 6 | 6,6 | V |
| Collector-emitter saturation voltage | V_{CEsat} | | 15 | | | 35 | 25 125 150 | | 1,48 1,64 1,68 | 1,75 | V |
| Collector-emitter cut-off current | I_{CES} | | 0 | 1200 | | | 25 | | | 0,08 | mA |
| Gate-emitter leakage current | I_{GES} | | 20 | 0 | | | 25 | | | 0,5 | μ A |
| Internal gate resistance | r_g | | | | | | | | none | | Ω |
| Input capacitance | C_{ies} | | | | | | | | 8000 | | pF |
| Output capacitance | C_{oes} | | 0 | 10 | | 25 | | | 280 | | |
| Reverse transfer capacitance | C_{res} | | | | | | | | 95 | | |
| Gate charge | Q_g | | 15 | 600 | 35 | | 25 | | 300 | | nC |

Thermal

| Parameter | Symbol | Value | Unit |
|-------------------------------------|---------------|------------------------------------|------|
| Thermal resistance junction to sink | $R_{th(j-s)}$ | $\lambda_{paste} = 3,4$ W/mK (PSX) | K/W |

Dynamic

| Parameter | Symbol | $R_{gon} = 8 \Omega$ $R_{goff} = 8 \Omega$ | V_{GS} [V] | V_{GE} [V] | V_{DS} [V] | I_D [A] | T_j [°C] | Min | Typ | Max | Unit |
|-----------------------------|--------------|--|--------------|--------------|--------------|-----------|------------------|-----|----------------------|-----|------|
| Turn-on delay time | $t_{d(on)}$ | | | | | | 25 125 150 | | 124 122 121 | | ns |
| Rise time | t_r | | | | | | 25 125 150 | | 14 17 18 | | |
| Turn-off delay time | $t_{d(off)}$ | | | | | | 25 125 150 | | 179 203 208 | | |
| Fall time | t_f | | | | | | 25 125 150 | | 95 118 119 | | |
| Turn-on energy (per pulse) | E_{on} | $Q_{tFWD} = 4,3 \mu$ C $Q_{tFWD} = 6,2 \mu$ C $Q_{tFWD} = 6,9 \mu$ C | | | | | 25 125 150 | | 1,45 1,92 2,09 | | mWs |
| Turn-off energy (per pulse) | E_{off} | | | | | | 25 125 150 | | 2,40 3,17 3,42 | | |



Characteristic Values

| Parameter | Symbol | Conditions | | | | | Value | | | Unit |
|-----------|--------|--------------|--------------|-----------|------------|-----|-------|-----|--|------|
| | | V_{GE} [V] | V_{CE} [V] | I_C [A] | T_j [°C] | Min | Typ | Max | | |

Inverter Diode

Static

| Parameter | Symbol | V_{GE} [V] | V_{CE} [V] | I_C [A] | T_j [°C] | Min | Typ | Max | Unit |
|-------------------------|--------|--------------|--------------|-----------|------------------|-----|----------------------|-----|------|
| Forward voltage | V_F | | | 35 | 25 125 150 | | 1,66 1,76 1,75 | 2,1 | V |
| Reverse leakage current | I_R | | 1200 | | 25 | | | 40 | μA |

Thermal

| Parameter | Symbol | Conditions | Value | Unit |
|-------------------------------------|---------------|------------------------------------|-------|------|
| Thermal resistance junction to sink | $R_{th(j-s)}$ | $\lambda_{paste} = 3,4$ W/mK (PSX) | 1,27 | K/W |

Dynamic

| Parameter | Symbol | V_{GE} [V] | V_{CE} [V] | I_C [A] | T_j [°C] | Min | Typ | Max | Unit |
|---------------------------------------|----------------------|---|--------------|-----------|------------------|------------------|----------------------|-----|------|
| Peak recovery current | I_{RRM} | | | | 25 125 150 | | 77 76 77 | | A |
| Reverse recovery time | t_{rr} | | | | 25 125 150 | | 157 284 311 | | ns |
| Recovered charge | Q_r | $di/dt = 2681$ A/μs $di/dt = 2670$ A/μs $di/dt = 2690$ A/μs | ±15 | 600 | 35 | 25 125 150 | 4,34 6,18 6,90 | | μC |
| Reverse recovered energy | E_{rec} | | | | 25 125 150 | | 1,96 2,82 3,13 | | mWs |
| Peak rate of fall of recovery current | $(di_{rr}/dt)_{max}$ | | | | 25 125 150 | | 2734 2205 2101 | | A/μs |

Thermistor

| Parameter | Symbol | Conditions | Value | Unit |
|----------------------------|----------------|---------------------|-------|---------------|
| Rated resistance | R | | 25 | kΩ |
| Deviation of R_{100} | $\Delta_{R/R}$ | $R_{100} = 401,3$ Ω | 100 | -12,5 12,5 |
| Power dissipation | P | | 25 | 5 |
| Power dissipation constant | | | 25 | 1,3 |
| B-value | $B_{(25/50)}$ | Tol. ±3% | 25 | 3612 |
| B-value | $B_{(25/100)}$ | Tol. ±3% | 25 | 3650 |
| Vincotech NTC Reference | | | | U |



Inverter Switch Characteristics

figure 1. IGBT

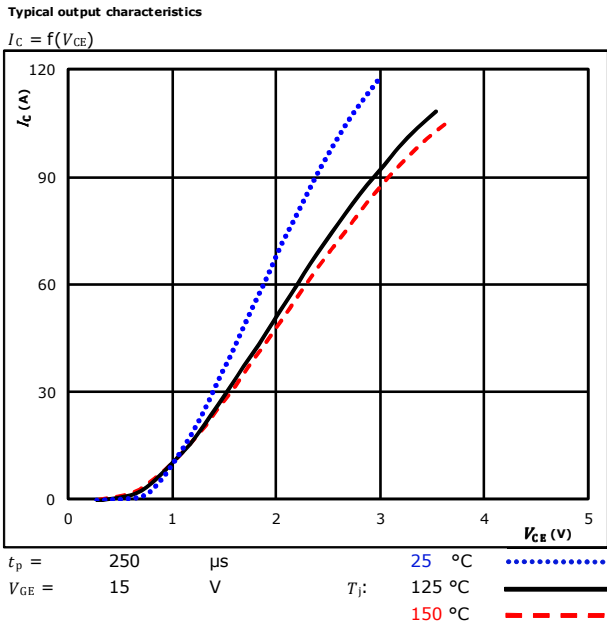


figure 2. IGBT

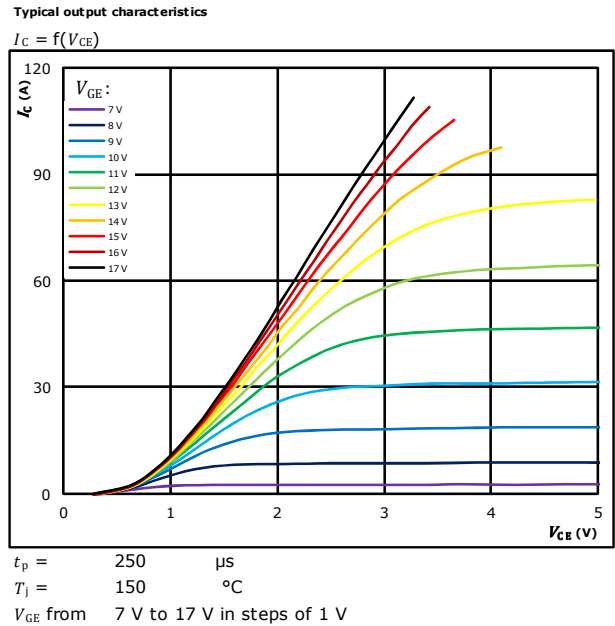


figure 3. IGBT

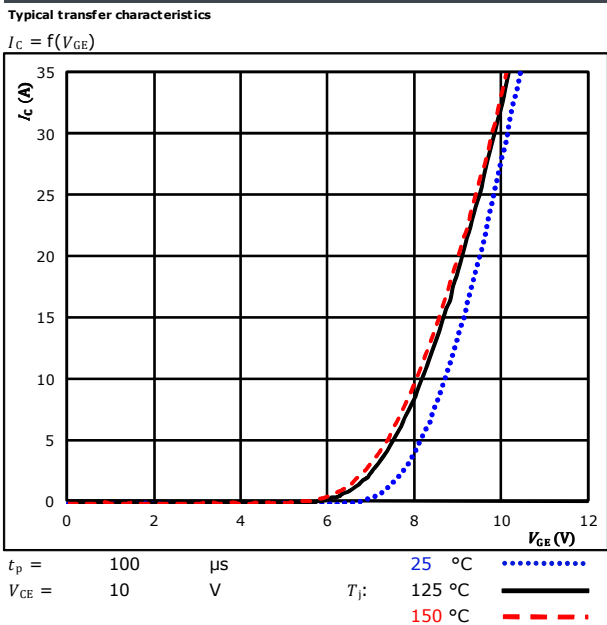
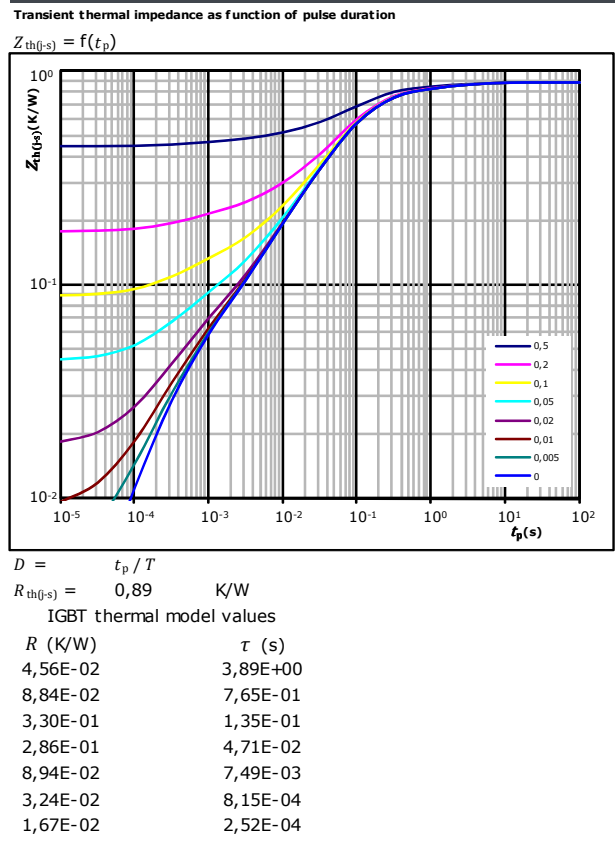


figure 4. IGBT



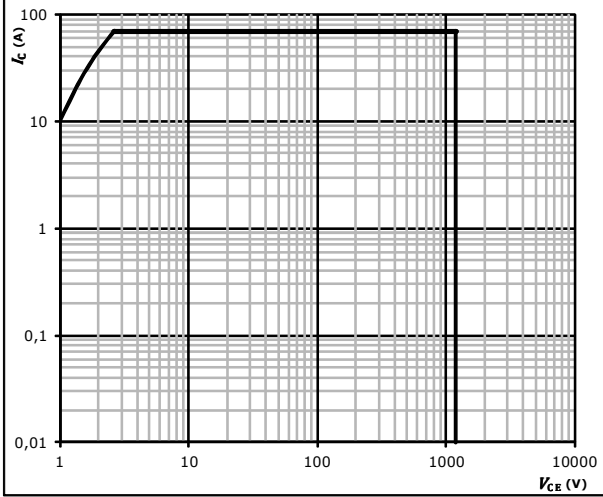


Inverter Switch Characteristics

figure 5. IGBT

Safe operating area

$$I_C = f(V_{CE})$$



- $D =$ single pulse
- $T_s =$ 80 °C
- $V_{GE} =$ ±15 V
- $T_j = T_{jmax}$



Inverter Diode Characteristics

figure 1. **FWD**

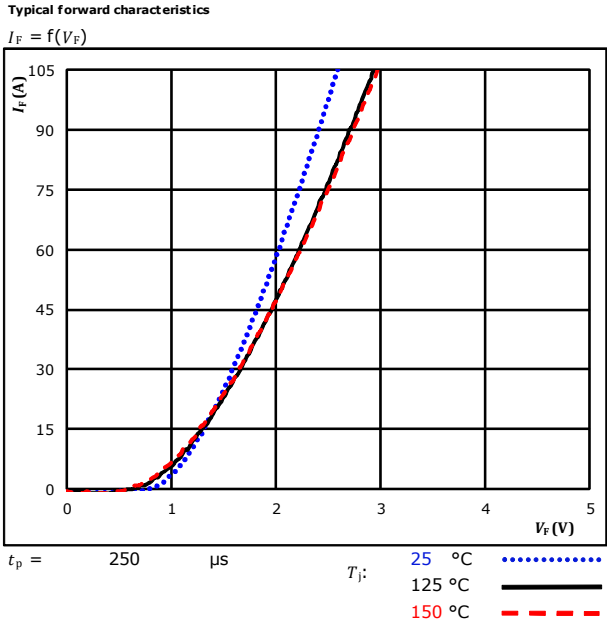
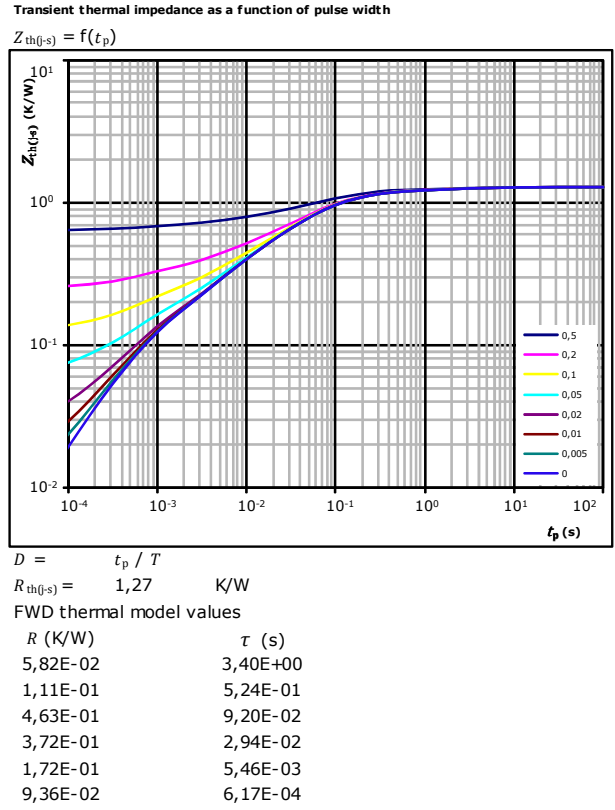
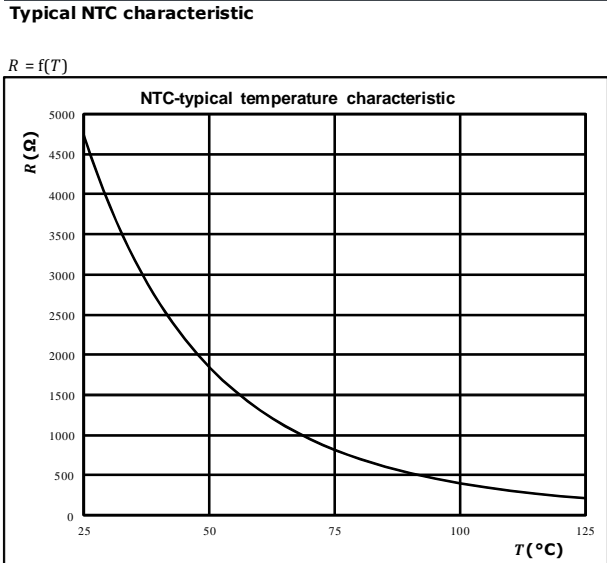


figure 2. **FWD**



Thermistor Characteristics

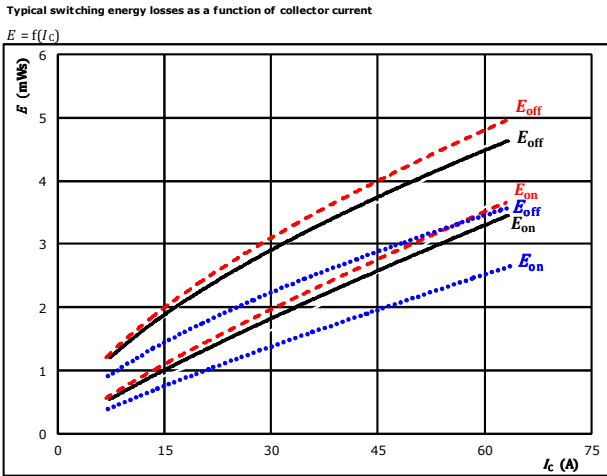
figure 1. **Thermistor**





Inverter Switching Characteristics

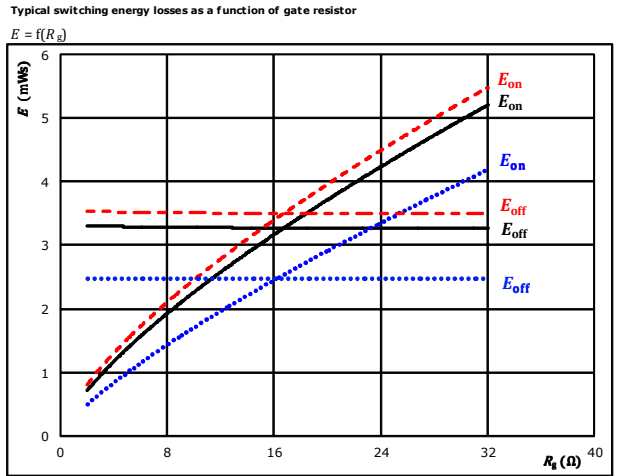
figure 1. IGBT



With an inductive load at
 $V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $R_{gon} = 8$ Ω
 $R_{goff} = 8$ Ω

T_j : 25 °C (dotted blue), 125 °C (solid black), 150 °C (dashed red)

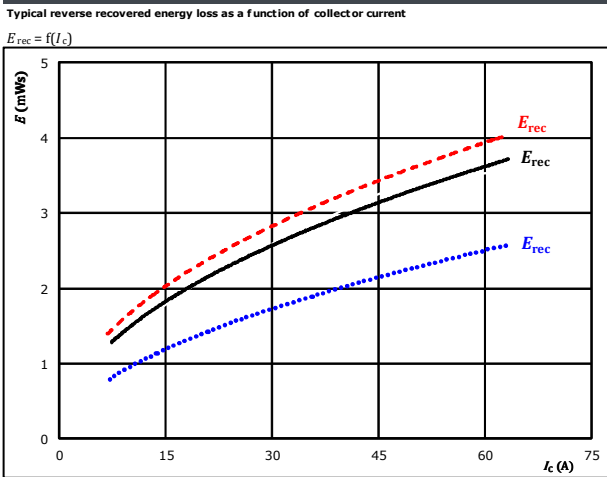
figure 2. IGBT



With an inductive load at
 $V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $I_c = 35$ A

T_j : 25 °C (dotted blue), 125 °C (solid black), 150 °C (dashed red)

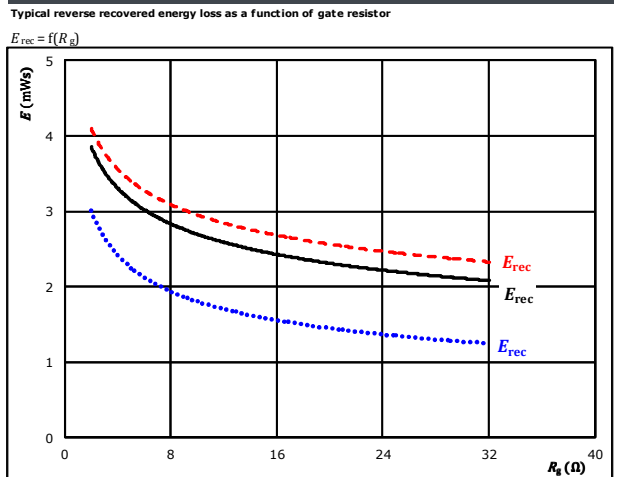
figure 3. FWD



With an inductive load at
 $V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $R_{gon} = 8$ Ω

T_j : 25 °C (dotted blue), 125 °C (solid black), 150 °C (dashed red)

figure 4. FWD



With an inductive load at
 $V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $I_c = 35$ A

T_j : 25 °C (dotted blue), 125 °C (solid black), 150 °C (dashed red)

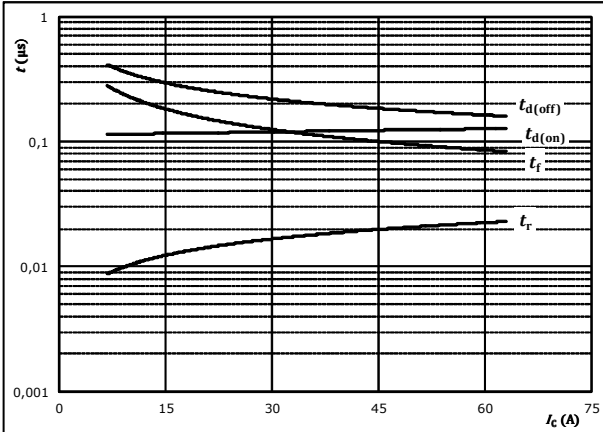


Inverter Switching Characteristics

figure 5. IGBT

Typical switching times as a function of collector current

$$t = f(I_c)$$



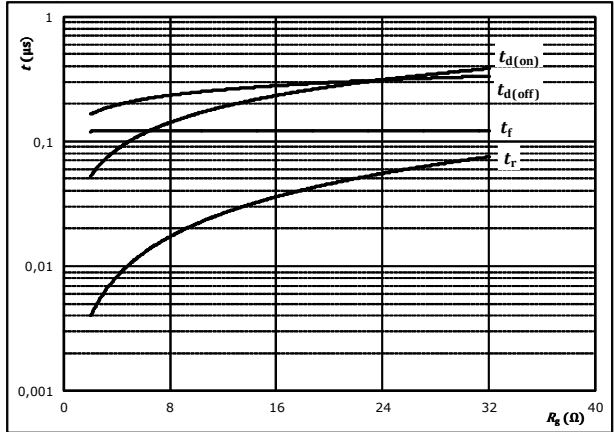
With an inductive load at

| | | |
|--------------|-----|----|
| $T_j =$ | 150 | °C |
| $V_{CE} =$ | 600 | V |
| $V_{GE} =$ | ±15 | V |
| $R_{gon} =$ | 8 | Ω |
| $R_{goff} =$ | 8 | Ω |

figure 6. IGBT

Typical switching times as a function of gate resistor

$$t = f(R_g)$$



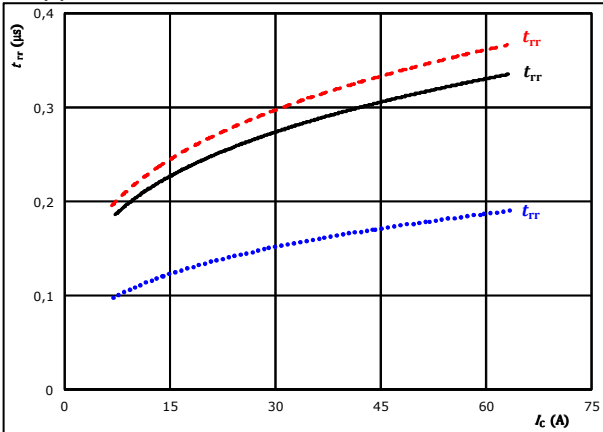
With an inductive load at

| | | |
|------------|-----|----|
| $T_j =$ | 150 | °C |
| $V_{CE} =$ | 600 | V |
| $V_{GE} =$ | ±15 | V |
| $I_c =$ | 35 | A |

figure 7. FWD

Typical reverse recovery time as a function of collector current

$$t_{rr} = f(I_c)$$

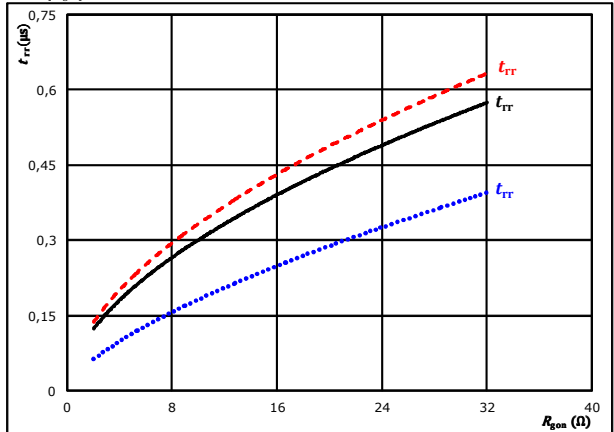


| | | | | | | |
|----|-------------|-----|---|--------|--------|-------|
| At | $V_{CE} =$ | 600 | V | $T_j:$ | 25 °C | |
| | $V_{GE} =$ | ±15 | V | | 125 °C | ———— |
| | $R_{gon} =$ | 8 | Ω | | 150 °C | ----- |

figure 8. FWD

Typical reverse recovery time as a function of IGBT turn on gate resistor

$$t_{rr} = f(R_{gon})$$

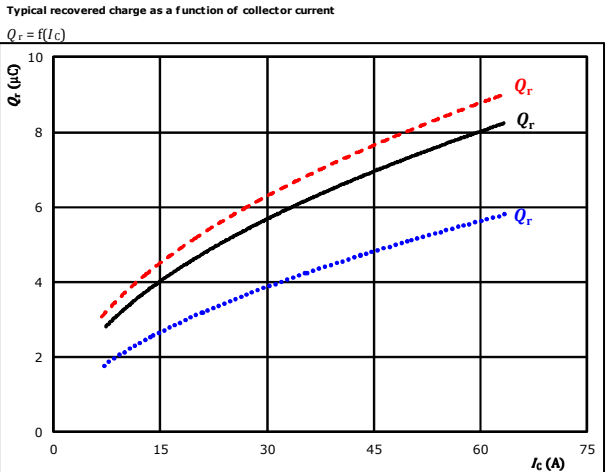


| | | | | | | |
|----|------------|-----|---|--------|--------|-------|
| At | $V_{CE} =$ | 600 | V | $T_j:$ | 25 °C | |
| | $V_{GE} =$ | ±15 | V | | 125 °C | ———— |
| | $I_c =$ | 35 | A | | 150 °C | ----- |



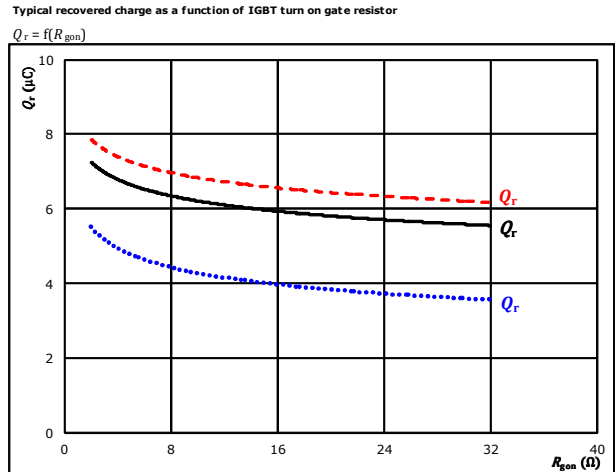
Inverter Switching Characteristics

figure 9. FWD



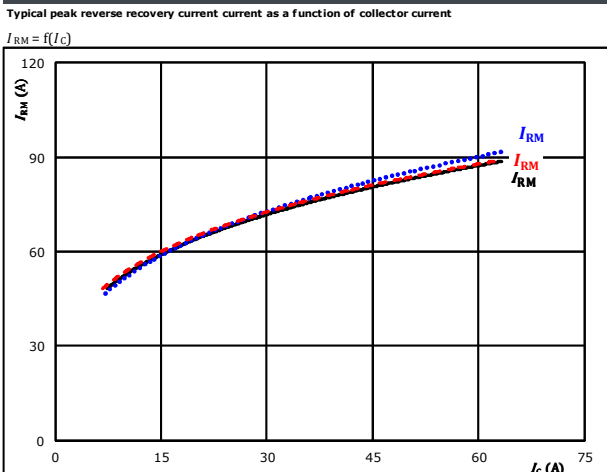
At $V_{CE} = 600$ V $T_j = 25$ °C
 $V_{GE} = \pm 15$ V $T_j = 125$ °C ———
 $R_{gpn} = 8$ Ω $T_j = 150$ °C - - - - -

figure 10. FWD



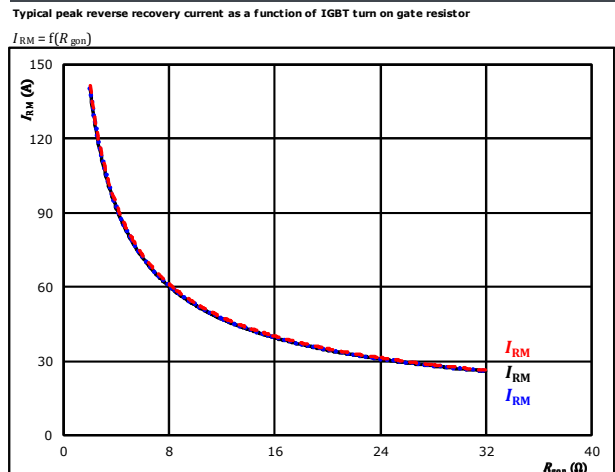
At $V_{CE} = 600$ V $T_j = 25$ °C
 $V_{GE} = \pm 15$ V $T_j = 125$ °C ———
 $I_c = 35$ A $T_j = 150$ °C - - - - -

figure 11. FWD



At $V_{CE} = 600$ V $T_j = 25$ °C
 $V_{GE} = \pm 15$ V $T_j = 125$ °C ———
 $R_{gpn} = 8$ Ω $T_j = 150$ °C - - - - -

figure 12. FWD



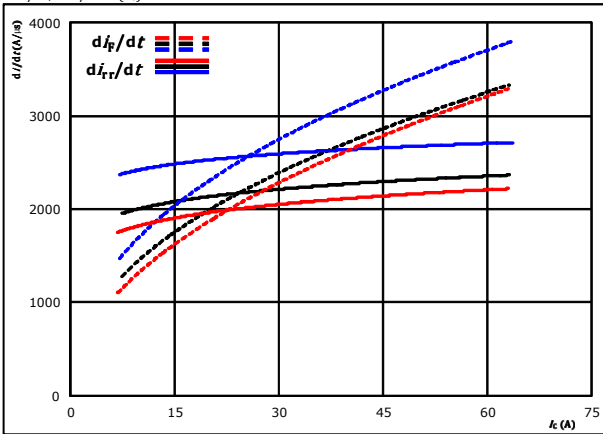
At $V_{CE} = 600$ V $T_j = 25$ °C
 $V_{GE} = \pm 15$ V $T_j = 125$ °C ———
 $I_c = 35$ A $T_j = 150$ °C - - - - -



Inverter Switching Characteristics

figure 13. FWD

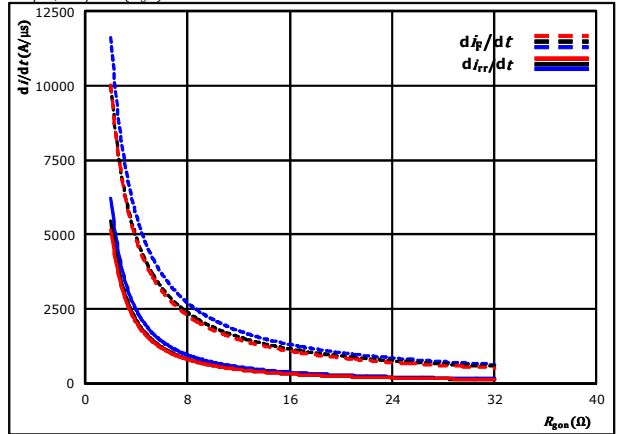
Typical rate of fall of forward and reverse recovery current as a function of collector current
 $di_f/dt, di_{rr}/dt = f(I_c)$



At $V_{CE} = 600$ V $T_j = 25$ °C
 $V_{GE} = \pm 15$ V $T_j = 125$ °C ———
 $R_{g(on)} = 8$ Ω $T_j = 150$ °C - - - - -

figure 14. FWD

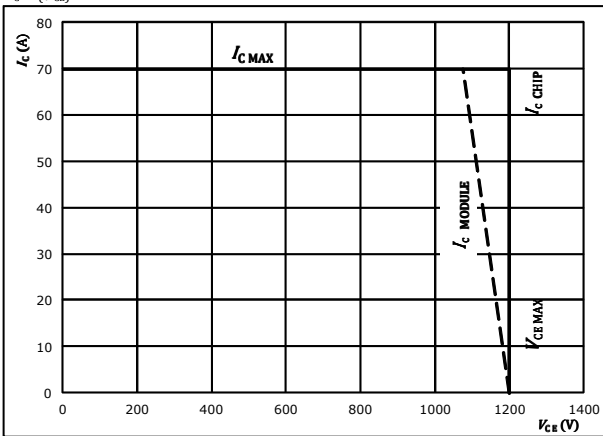
Typical rate of fall of forward and reverse recovery current as a function of IGBT turn on gate resistor
 $di_f/dt, di_{rr}/dt = f(R_{g(on)})$



At $V_{CE} = 600$ V $T_j = 25$ °C
 $V_{GE} = \pm 15$ V $T_j = 125$ °C ———
 $I_c = 35$ A $T_j = 150$ °C - - - - -

figure 15. IGBT

Reverse bias safe operating area
 $I_c = f(V_{CE})$



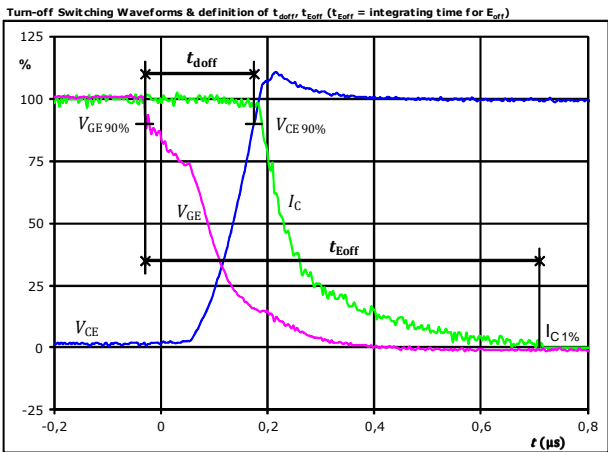
At $T_j = 175$ °C
 $R_{g(on)} = 8$ Ω
 $R_{g(off)} = 8$ Ω



Inverter Switching Definitions

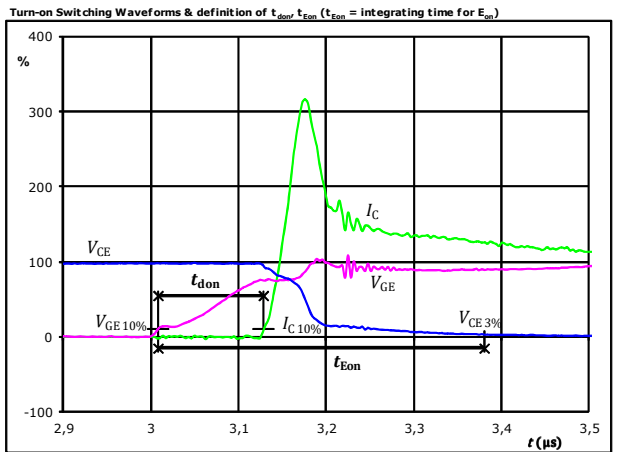
| General conditions | | |
|--------------------|---|--------|
| T_j | = | 125 °C |
| R_{gon} | = | 8 Ω |
| R_{goff} | = | 8 Ω |

figure 1. IGBT



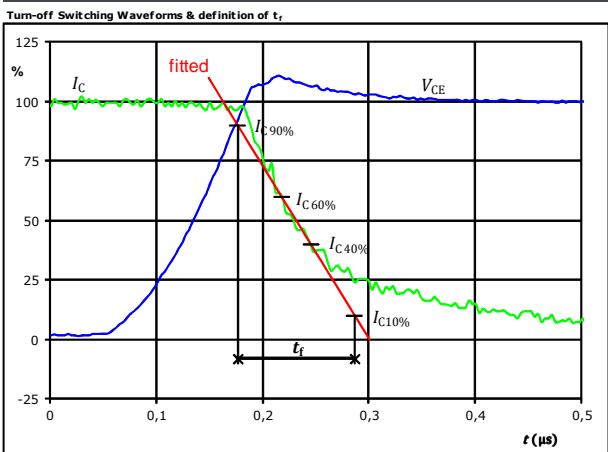
| | | |
|-------------------|-------|----|
| $V_{CE}(0\%) =$ | -15 | V |
| $V_{GE}(100\%) =$ | 15 | V |
| $V_C(100\%) =$ | 600 | V |
| $I_C(100\%) =$ | 35 | A |
| $t_{doff} =$ | 0,203 | μs |
| $t_{Eoff} =$ | 0,739 | μs |

figure 2. IGBT



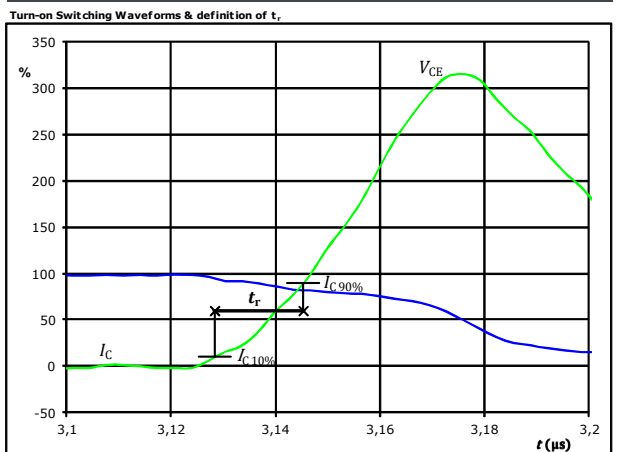
| | | |
|-------------------|-------|----|
| $V_{CE}(0\%) =$ | -15 | V |
| $V_{GE}(100\%) =$ | 15 | V |
| $V_C(100\%) =$ | 600 | V |
| $I_C(100\%) =$ | 35 | A |
| $t_{don} =$ | 0,122 | μs |
| $t_{Eon} =$ | 0,372 | μs |

figure 3. IGBT



| | | |
|----------------|-------|----|
| $V_C(100\%) =$ | 600 | V |
| $I_C(100\%) =$ | 35 | A |
| $t_f =$ | 0,118 | μs |

figure 4. IGBT



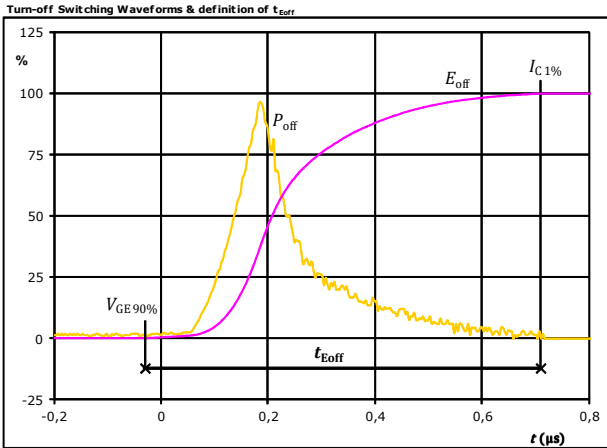
| | | |
|----------------|-------|----|
| $V_C(100\%) =$ | 600 | V |
| $I_C(100\%) =$ | 35 | A |
| $t_r =$ | 0,017 | μs |



Vincotech

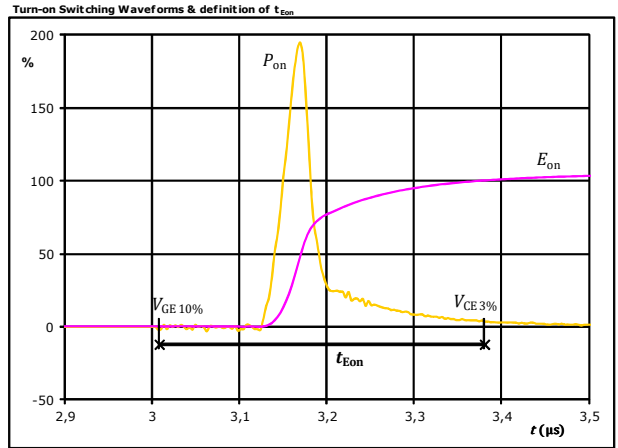
Inverter Switching Characteristics

figure 5. IGBT



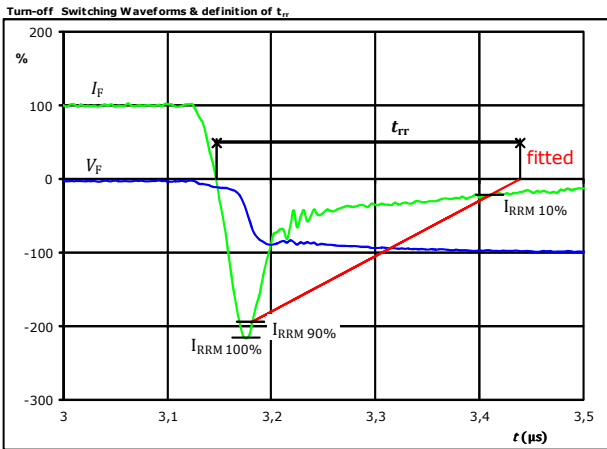
| | | |
|--------------------|-------|---------|
| $P_{off}(100\%) =$ | 20,99 | kW |
| $E_{off}(100\%) =$ | 3,17 | mJ |
| $t_{Eoff} =$ | 0,74 | μ s |

figure 6. IGBT



| | | |
|-------------------|-------|---------|
| $P_{on}(100\%) =$ | 20,99 | kW |
| $E_{on}(100\%) =$ | 1,92 | mJ |
| $t_{Eon} =$ | 0,37 | μ s |

figure 7. FWD

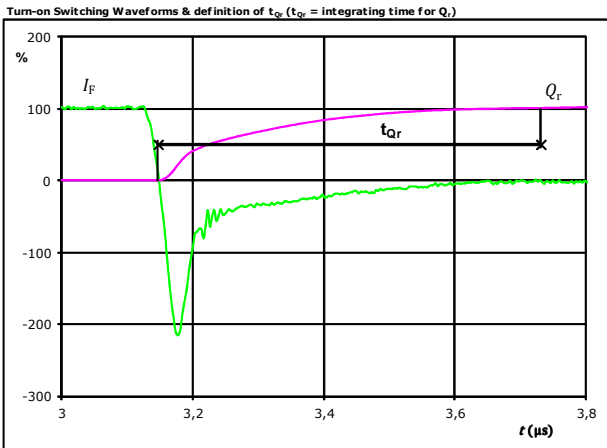


| | | |
|--------------------|-------|---------|
| $V_F(100\%) =$ | 600 | V |
| $I_F(100\%) =$ | 35 | A |
| $I_{RRM}(100\%) =$ | -76 | A |
| $t_{rr} =$ | 0,284 | μ s |



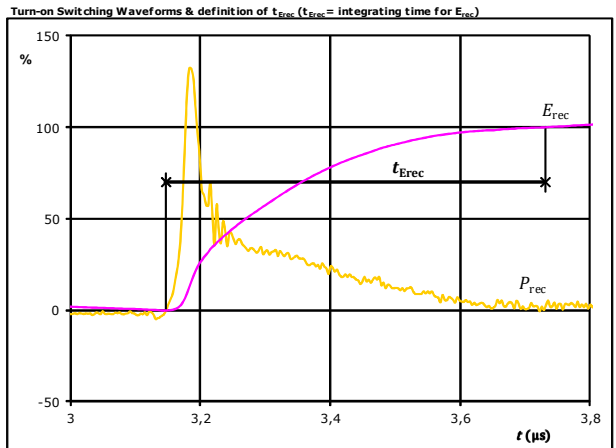
Inverter Switching Characteristics

figure 8. FWD



| | | |
|----------------|------|---------------|
| I_F (100%) = | 35 | A |
| Q_r (100%) = | 6,18 | μC |
| t_{Qr} = | 0,58 | μs |

figure 9. FWD



| | | |
|--------------------|-------|---------------|
| P_{rec} (100%) = | 20,99 | kW |
| E_{rec} (100%) = | 2,82 | mJ |
| t_{Erec} = | 0,58 | μs |



10-F1126PA035M7-L827F09
10-P1126PA035M7-L827F09Y
 datasheet

Vincotech

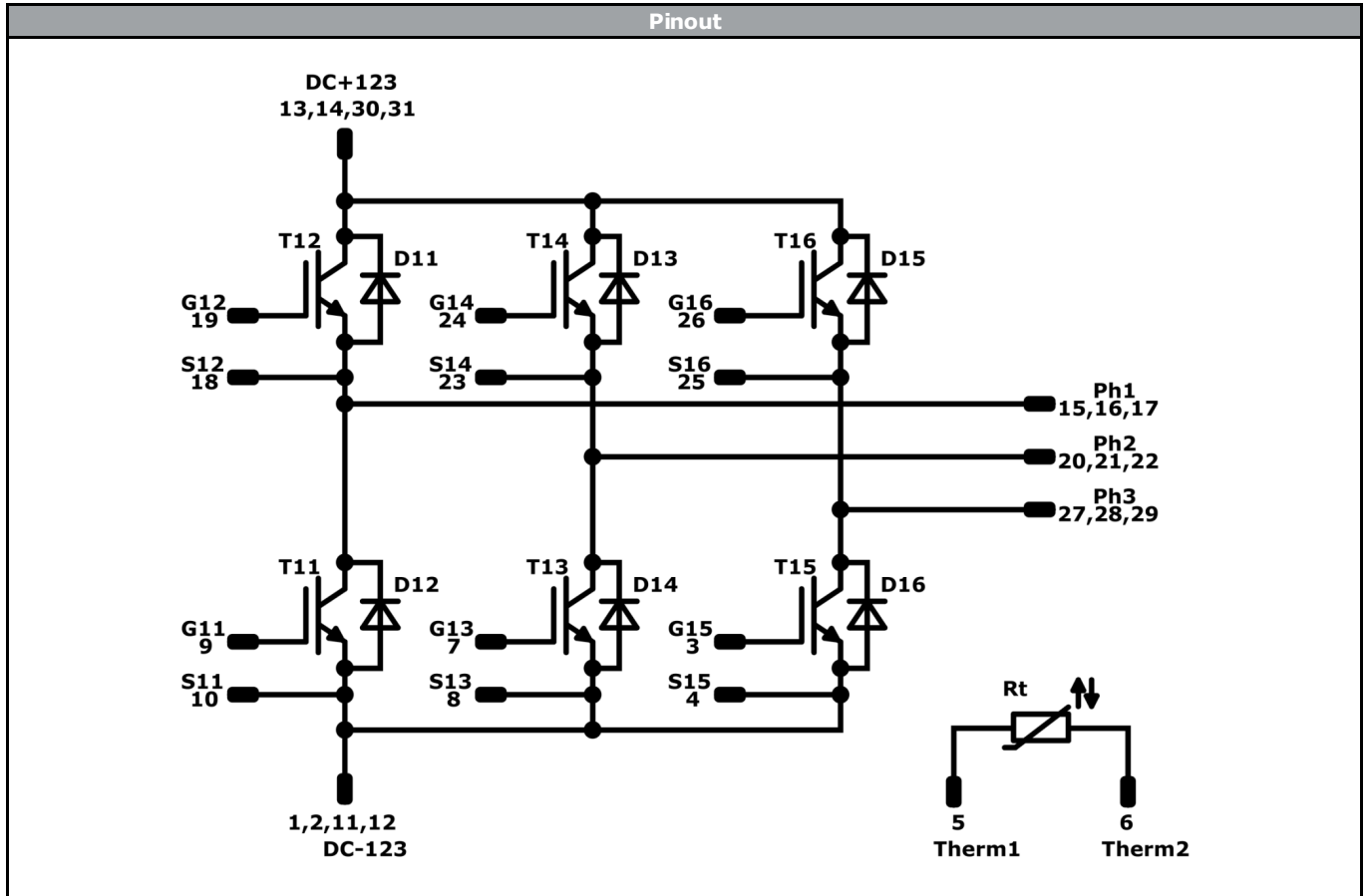
| Ordering Code & Marking | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | |
|--|-----------------------------|------------|--------------------------|-----------|-------|--------|------|------|--|-----------|----------|-----|--------|-----------------------------|--|------|--------|-------|------|------------|----------|------------|--------|-----------|--|--|---------|-------|------|------|--|--|
| Version | | | Ordering Code | | | | | | | | | | | | | | | | | | | | | | | | | | | | | |
| without thermal paste 17 mm housing with solder pins | | | 10-F1126PA035M7-L827F09 | | | | | | | | | | | | | | | | | | | | | | | | | | | | | |
| without thermal paste 17 mm housing with press-fit pins | | | 10-P1126PA035M7-L827F09Y | | | | | | | | | | | | | | | | | | | | | | | | | | | | | |
| <table border="1"> <thead> <tr> <th rowspan="2">Text</th> <th colspan="2">Name</th> <th>Date code</th> <th>UL & VIN</th> <th>Lot</th> <th>Serial</th> </tr> <tr> <th colspan="2">NN-NNNNNNNNNNNNNNNN-TTTTTTW</th> <th>WWYY</th> <th>UL VIN</th> <th>LLLLL</th> <th>SSSS</th> </tr> </thead> <tbody> <tr> <td rowspan="2">Datamatrix</td> <th>Type&Ver</th> <th>Lot number</th> <th>Serial</th> <th>Date code</th> <td></td> <td></td> </tr> <tr> <td>TTTTTTW</td> <td>LLLLL</td> <td>SSSS</td> <td>WWYY</td> <td></td> <td></td> </tr> </tbody> </table> | | | | | | | Text | Name | | Date code | UL & VIN | Lot | Serial | NN-NNNNNNNNNNNNNNNN-TTTTTTW | | WWYY | UL VIN | LLLLL | SSSS | Datamatrix | Type&Ver | Lot number | Serial | Date code | | | TTTTTTW | LLLLL | SSSS | WWYY | | |
| Text | Name | | Date code | UL & VIN | Lot | Serial | | | | | | | | | | | | | | | | | | | | | | | | | | |
| | NN-NNNNNNNNNNNNNNNN-TTTTTTW | | WWYY | UL VIN | LLLLL | SSSS | | | | | | | | | | | | | | | | | | | | | | | | | | |
| Datamatrix | Type&Ver | Lot number | Serial | Date code | | | | | | | | | | | | | | | | | | | | | | | | | | | | |
| | TTTTTTW | LLLLL | SSSS | WWYY | | | | | | | | | | | | | | | | | | | | | | | | | | | | |

| Pin table | | | | Outline | |
|-----------|-------|-------|-----------|---------|--|
| Pin | X | Y | Functions | | |
| 1 | 52,6 | 0 | DC-123 | | |
| 2 | 49,9 | 0 | DC-123 | | |
| 3 | 42,65 | 0 | G15 | | |
| 4 | 39,65 | 0 | S15 | | |
| 5 | 35,15 | 0 | Therm1 | | |
| 6 | 28,4 | 0 | Therm2 | | |
| 7 | 24 | 0 | G13 | | |
| 8 | 21 | 0 | S13 | | |
| 9 | 12,2 | 0 | G11 | | |
| 10 | 9,2 | 0 | S11 | | |
| 11 | 2,7 | 0 | DC-123 | | |
| 12 | 0 | 0 | DC-123 | | |
| 13 | 0 | 14,65 | DC+123 | | |
| 14 | 2,7 | 14,65 | DC+123 | | |
| 15 | 0 | 28,6 | Ph1 | | |
| 16 | 2,7 | 28,6 | Ph1 | | |
| 17 | 5,4 | 28,6 | Ph1 | | |
| 18 | 9,6 | 28,6 | S12 | | |
| 19 | 12,6 | 28,6 | G12 | | |
| 20 | 19,6 | 28,6 | Ph2 | | |
| 21 | 22,3 | 28,6 | Ph2 | | |
| 22 | 25 | 28,6 | Ph2 | | |
| 23 | 29,7 | 28,6 | S14 | | |
| 24 | 32,7 | 28,6 | G14 | | |
| 25 | 39,7 | 28,6 | S16 | | |
| 26 | 42,7 | 28,6 | G16 | | |
| 27 | 47,2 | 28,6 | Ph3 | | |
| 28 | 49,9 | 28,6 | Ph3 | | |
| 29 | 52,6 | 28,6 | Ph3 | | |
| 30 | 52,6 | 14,65 | DC+123 | | |
| 31 | 49,9 | 14,65 | DC+123 | | |

Tolerance of pinpositions ±0,5mm at the end of pins
Dimension of coordinate axis is only offset without tolerance



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| Identification | | | | | |
|------------------------------|------------------|----------------|----------------|-----------------|----------------|
| ID | Component | Voltage | Current | Function | Comment |
| T11, T12, T13, T14, T15, T16 | IGBT | 1200 V | 35 A | Inverter Switch | |
| D11, D12, D13, D14, D15, D16 | FWD | 1200 V | 35 A | Inverter Diode | |
| Rt | NTC | | | Thermistor | |




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| Packaging instruction | | | |
|---------------------------------------|------|----------|-------------|
| Standard packaging quantity (SPQ) 100 | >SPQ | Standard | <SPQ Sample |

| Handling instruction |
|---|
| Handling instructions for <i>flow 1</i> packages see vincotech.com website. |

| Package data |
|--|
| Package data for <i>flow 1</i> packages see vincotech.com website. |

| UL recognition and file number |
|---|
| This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website.  |

| Document No.: | Date: | Modification: | Pages |
|--------------------------------|--------------|---------------|-------|
| 10-x1126PA035M7-L827F09x-D1-14 | 23 Nov. 2017 | | |

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